

**SuperMOS - PDFN3X3-8L -30V  $V_{DSS}$ , 13m $\Omega$   $R_{DS(on)}$ , -31A  $I_D$  P-channel MOSFET**

**1. Description**

The ESN7403 is P-Channel enhancement MOS Field Effect Transistor. Uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. Device is suitable for use in DC-DC conversion, power switch and charging circuit. Standard Product ESN7403 is Pb-free.

**2. Features**

- -30V,  $R_{DS(ON)}$ =13 m $\Omega$ (Typ),  $V_{GS}$ =-10V  
 $R_{DS(ON)}$ =17m $\Omega$ (Typ),  $V_{GS}$ =-4.5V
- Fast Switching
- High density cell design for low  $R_{DS(on)}$
- Material: Halogen free
- Reliable and rugged
- Avalanche Rated
- Low leakage current

**3. Applications**

- PWM applications
- Load switch
- Power management in portable/desktop PCs
- DC/DC conversion

**4. Ordering Information**

Part Number	Package	Marking	Material	Quantity per reel	Flammability Rating
ESN7403	PDFN3X3-8L	.ESN7403/LOT	Halogen free	5,000 PCS	UL 94V-0

**5. Pin Configuration and Functions**

Pin	Function	Outline	Circuit Diagram
4	Gate		
1/2/3	Source		
5/6/7/8	Drain		

## 6. Specification

### Absolute Maximum Rating & Thermal Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$BV_{DSS}$	-30	V
Gate-Source Voltage	$V_{GS}$	$\pm 25$	V
Continuous Drain Current	$I_D$	$T_C=25^\circ C$	-31
		$T_C=75^\circ C$	-24
Maximum Power Dissipation	$P_D$	$T_C=25^\circ C$	30
		$T_C=75^\circ C$	18
Pulsed Drain Current <sup>a</sup>	$I_{DM}$	-124	A
Operating Junction Temperature	$T_J$	150	°C
Storage Temperature Range	$T_{stg}$	-55 to +150	°C

### Thermal resistance ratings

Single Operation				
Parameter		Symbol	Typical	Unit
Junction-to-Ambient Thermal Resistance	$t \leq 10$ s	$R_{\theta JA}$	40	°C/W
Junction-to-Case Thermal Resistance	Steady State	$R_{\theta JC}$	4.2	

Note:

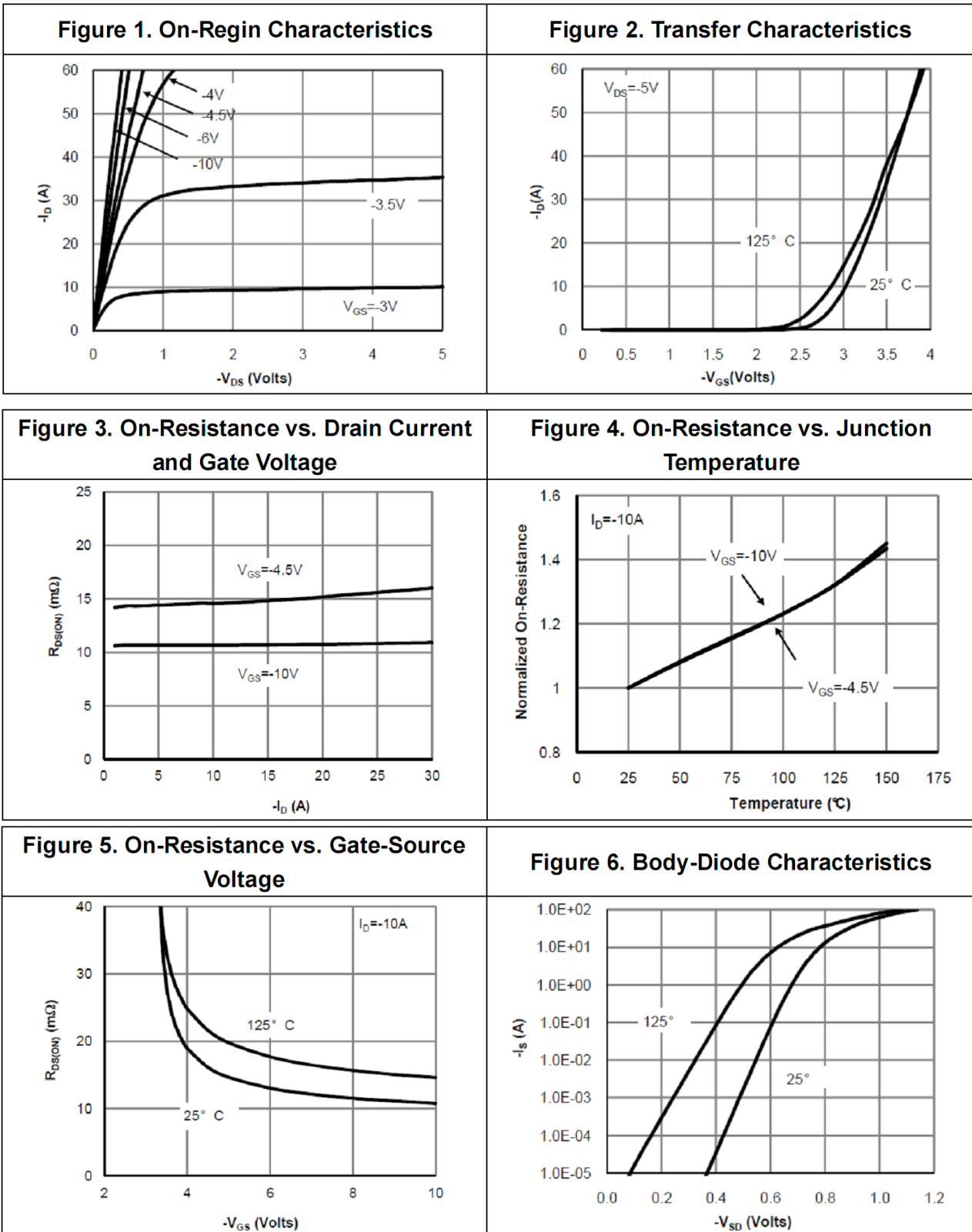
a: Repetitive rating, pulse width limited by junction temperature,  $t_p=10\mu s$ , Duty Cycle=1%

## Electrical Characteristics

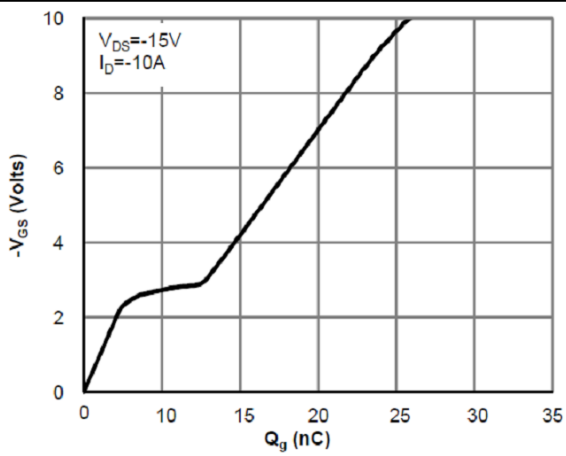
At TA = 25°C unless otherwise specified

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>OFF CHARACTERISTICS</b>						
Drain-to-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-30			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{GS}=0V, V_{DS}=-30V$			-1	$\mu A$
Gate-to-source Leakage Current	$I_{GSS}$	$V_{GS}=\pm 25V, V_{DS}=0V$			$\pm 100$	nA
<b>ON CHARACTERISTICS</b>						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=-250\mu A$	-1.0	-1.5	-2.0	V
Drain-to-source On-resistance	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-8A$		13	20	m $\Omega$
		$V_{GS}=-4.5V, I_D=-7A$		17	27	
<b>CHARGES, CAPACITANCES AND GATE RESISTANCE</b>						
Input Capacitance	$C_{ISS}$	$V_{GS}=0V$ $V_{DS}=-15V$ $f=1MHz$		1230		pF
Output Capacitance	$C_{OSS}$			160		
Reverse Transfer Capacitance	$C_{RSS}$			145		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS}=-10V$ $V_{DS}=-15V$ $I_D=-10A$		26.4		nC
Gate-to-Source Charge	$Q_{GS}$			6		
Gate-to-Drain Charge	$Q_{GD}$			4.3		
<b>SWITCHING CHARACTERISTICS</b>						
Turn-On Delay Time	$t_{d(ON)}$	$V_{GS}=-10V$ $V_{DS}=-15V$ $R_L=1\Omega$ $R_G=3\Omega$		18		ns
Rise Time	$t_r$			22		
Turn-Off Delay Time	$t_{d(OFF)}$			55		
Fall Time	$t_f$			42		
<b>BODY DIODE CHARACTERISTICS</b>						
Forward Voltage	$V_{SD}$	$V_{GS}=0V, I_{SD}=-10A$			-1.2	V

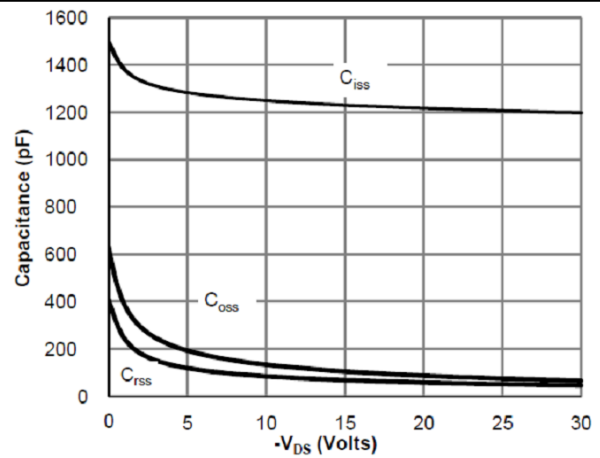
7. Typical Characteristic



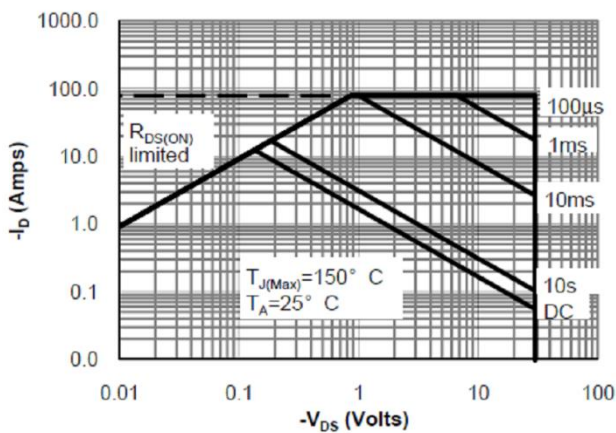
**Figure 7. Gate-Charge Characteristics**



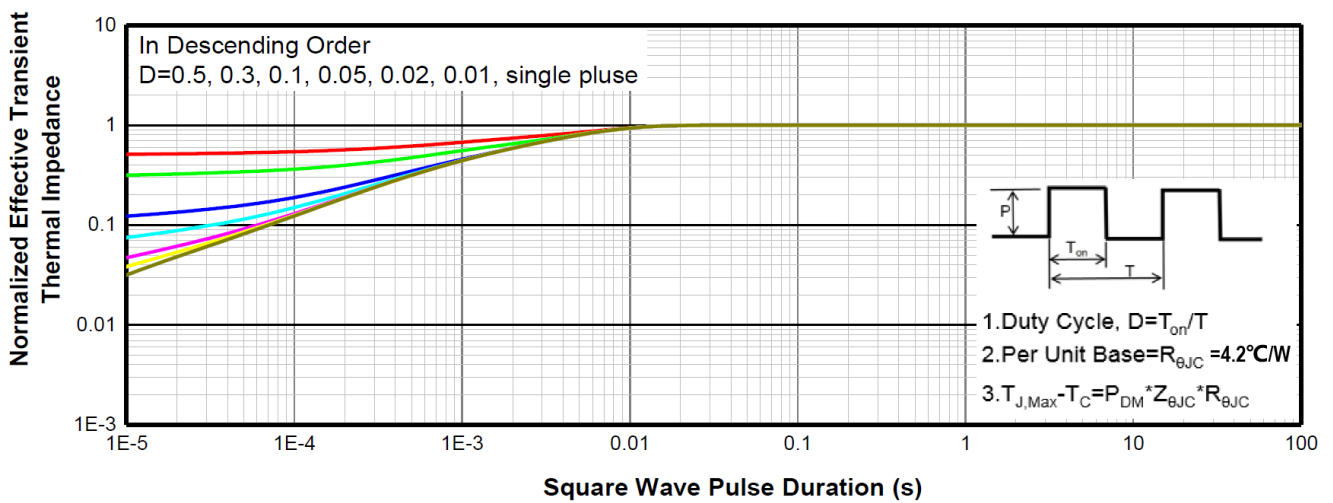
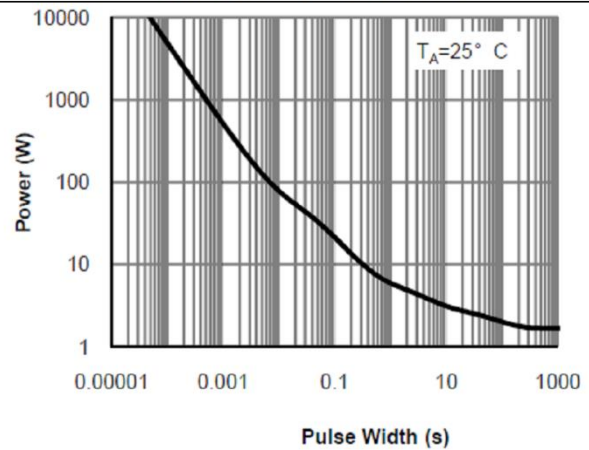
**Figure 8. Capacitance Characteristics**



**Figure 9. Maximum Forward Biased Safe Operating Area**

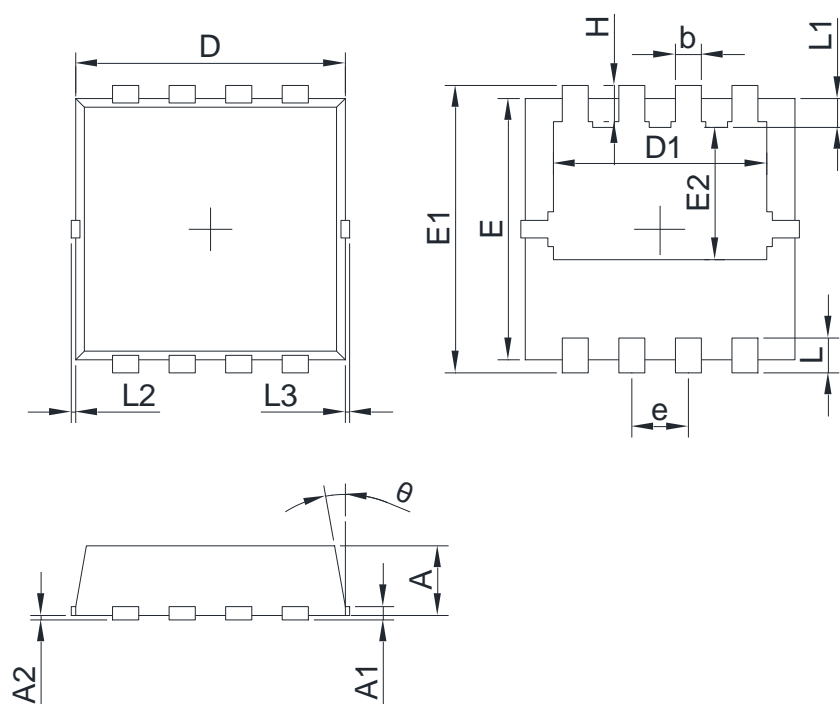


**Figure 10. Single Pulse Power Rating Junction-to-Ambient**



**Transient Thermal Response (Junction-to-Case)**

8. Dimension (PDFN3X3-8L)



Unit: mm

COMMON DIMENSIONS: UNITS OF MEASURE=MILLIMETER

SYMBOL	MILLIMETER			SYMBOL	MILLIMETER		
	MIN	Typ.	MAX		MIN	Typ.	MAX
A	0.700	0.800	0.900	b	0.200	0.300	0.400
A1	0.152 REF.			e	0.550	0.650	0.750
A2	0~0.05			L	0.300	0.400	0.500
D	3.000	3.100	3.200	L1	0.180	0.330	0.480
D1	2.300	2.450	2.600	L2	0~0.100		
E	2.900	3.000	3.100	L3	0~0.100		
E1	3.150	3.300	3.450	H	0.315	0.415	0.515
E2	1.320	1.520	1.720	θ	8°	10°	12°

Table-5 Product dimensions in millimeter

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